

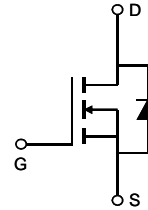
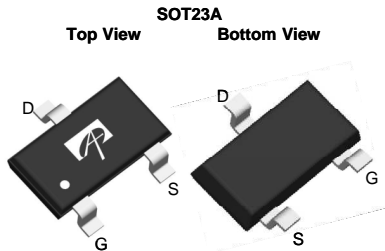
**General Description**

The AO3162 is fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications.

By providing low  $R_{DS(on)}$ ,  $C_{iss}$  and  $C_{rss}$  along with guaranteed avalanche capability this device can be adopted quickly into new and existing offline power supply designs.

**Product Summary**

$V_{DS}$	700V@150°C
$I_D$ (at $V_{GS}=10V$ )	0.034A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 500Ω


**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	600	V
Gate-Source Voltage	$V_{GS}$	±30	V
Continuous Drain Current <sup>A,F</sup>	$I_D$	$T_A=25^\circ\text{C}$	0.034
		$T_A=70^\circ\text{C}$	0.028
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	0.16	
Peak diode recovery $dv/dt$	$dv/dt$	5	V/ns
Power Dissipation <sup>A</sup>	$P_D$	$T_A=25^\circ\text{C}$	1.39
		$T_A=70^\circ\text{C}$	0.89
Junction and Storage Temperature Range	$T_J, T_{STG}$	-50 to 150	°C

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	$t \leq 10s$	70	90
		Steady-State	100	125
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	63	80	°C/W

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	600	-	-	V
		I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C	-	700	-	
BV <sub>DSS</sub> /ΔT <sub>J</sub>	Zero Gate Voltage Drain Current	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	-	0.69	-	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V	-	-	1	μA
		V <sub>DS</sub> =480V, T <sub>J</sub> =125°C	-	-	10	
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V	-	-	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =5V, I <sub>D</sub> =8μA	2.8	3.2	4.1	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =0.016A	-	154	500	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =40V, I <sub>D</sub> =0.016A	-	0.045	-	S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =0.016A, V <sub>GS</sub> =0V	-	0.74	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current		-	-	0.034	A
I <sub>SM</sub>	Maximum Body-Diode Pulsed Current		-	-	0.16	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	-	4.2	6	pF
C <sub>OSS</sub>	Output Capacitance		-	0.45	0.6	pF
C <sub>rSS</sub>	Reverse Transfer Capacitance		-	0.05	0.07	pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	14	28	42	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =400V, I <sub>D</sub> =0.01A	-	0.1	0.15	nC
Q <sub>gs</sub>	Gate Source Charge		-	0.03	0.05	nC
Q <sub>gd</sub>	Gate Drain Charge		-	0.05	0.08	nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =300V, I <sub>D</sub> =0.01A, R <sub>G</sub> =6Ω	-	13.8	20	ns
t <sub>r</sub>	Turn-On Rise Time		-	10	15	ns
t <sub>D(off)</sub>	Turn-Off DelayTime		-	39.2	57	ns
t <sub>f</sub>	Turn-Off Fall Time		-	13	19	ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =0.016A, dI/dt=100A/μs, V <sub>DS</sub> =300V	-	105	160	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =0.016A, dI/dt=100A/μs, V <sub>DS</sub> =300V	-	9.5	14.3	nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The SOA curve provides a single pulse rating.

F: The current rating is based on the t ≤ 10s thermal resistance rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

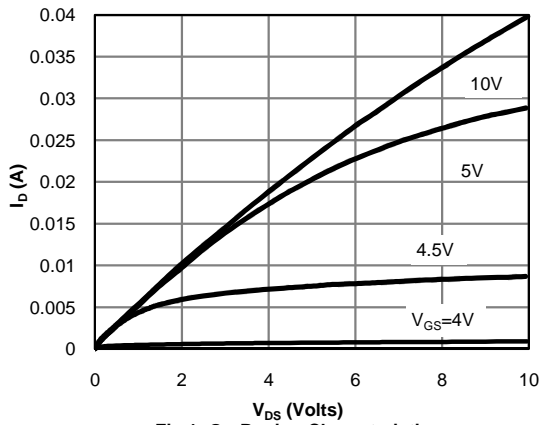


Fig 1: On-Region Characteristics

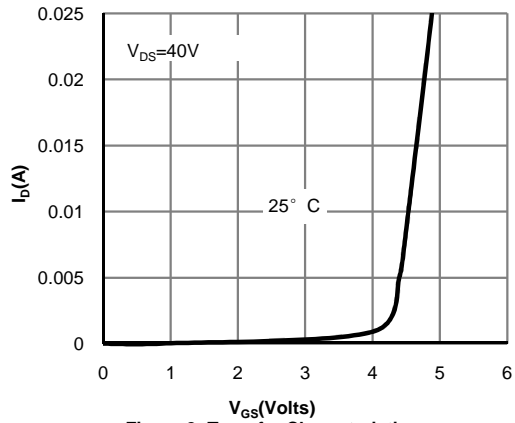


Figure 2: Transfer Characteristics

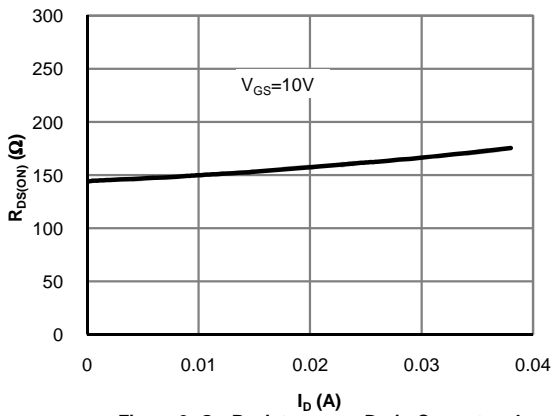


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

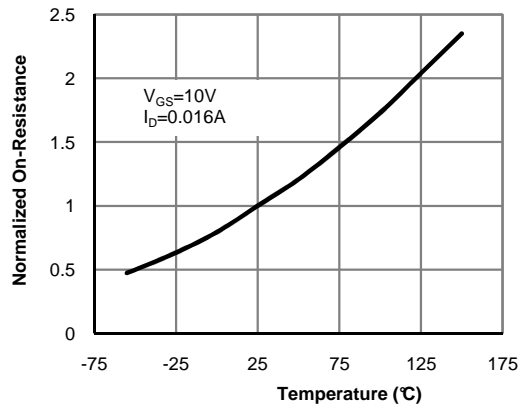


Figure 4: On-Resistance vs. Junction Temperature

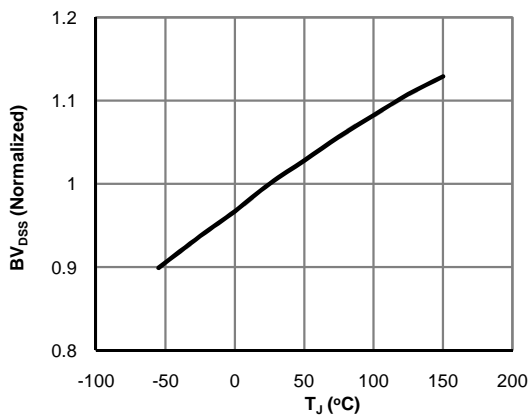


Figure 5: Break Down vs. Junction Temperature

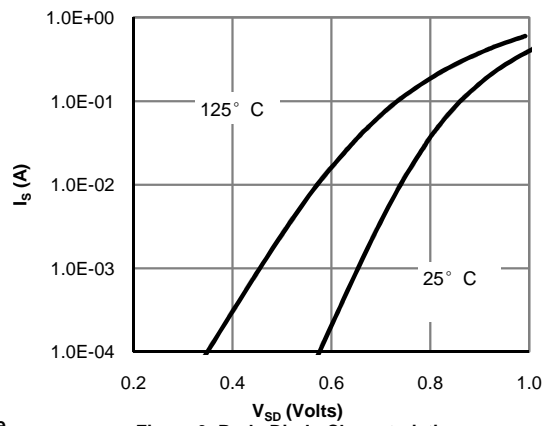


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

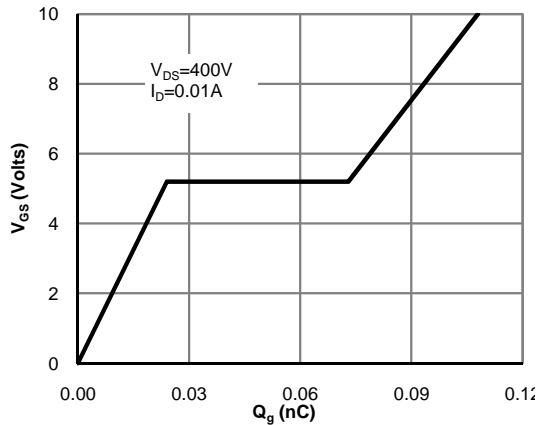


Figure 7: Gate-Charge Characteristics

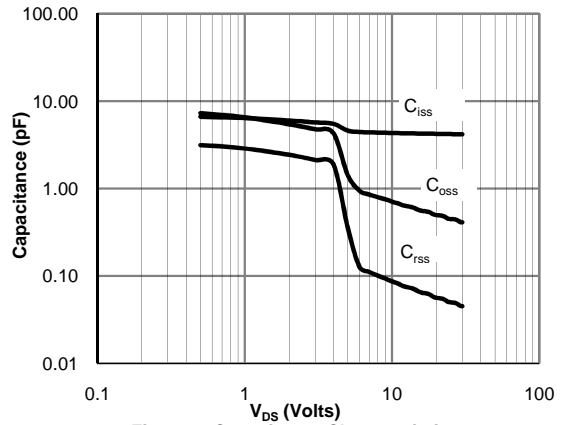


Figure 8: Capacitance Characteristics

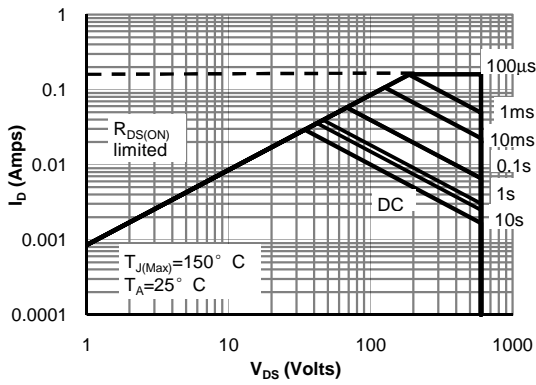


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

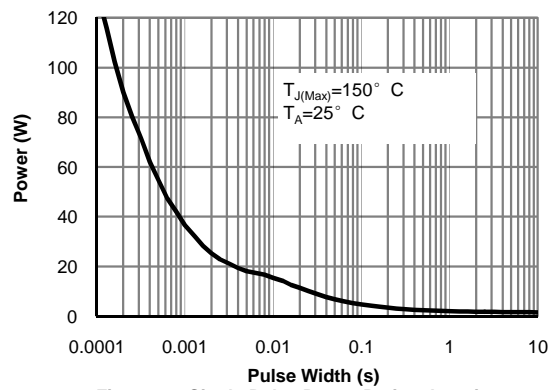


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

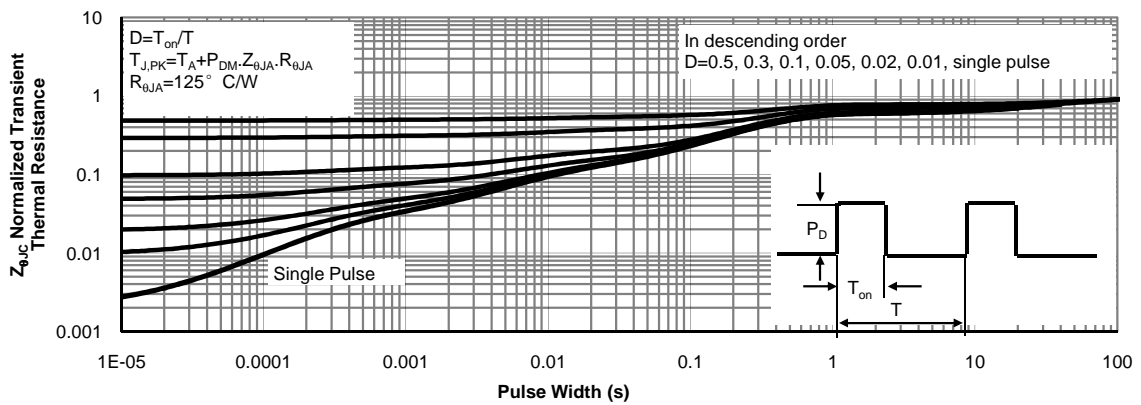
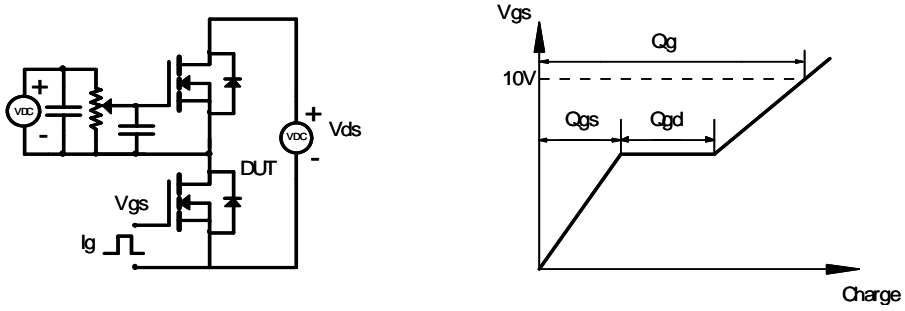
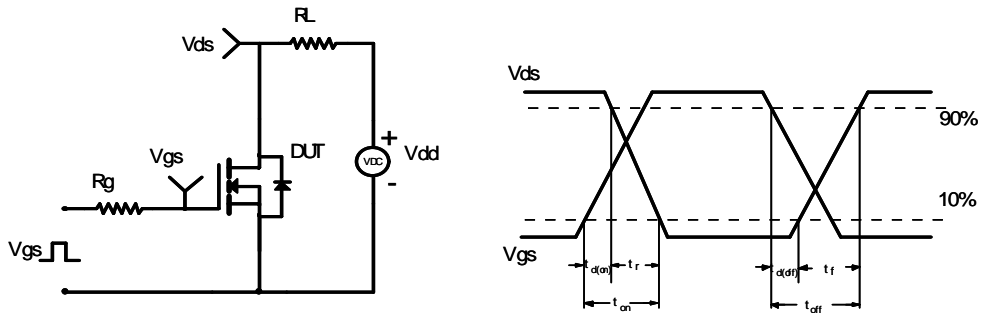


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)

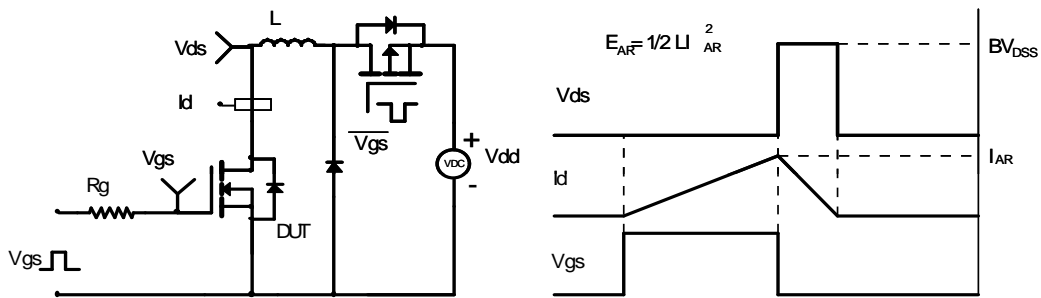
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

